REMARKS

Claim 1 calls for a process of forming a phase change memory. A phase change memory cell substrate is provided including a lower electrode in a first dielectric film. The lower electrode includes an upper and lower section. A portion of the first dielectric film is removed to cause the upper section to form a prominence. The resistivity of the prominence is increased.

The asserted prominence in Lowrey does not have any upper section that extends above the dielectric film. Therefore, reconsideration is requested of the rejections of claims 1 and 33.

Respectfully submitted,

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